

MOSFET – Power, Single N-Channel

40 V, 14 mΩ, 26 A

NVTFS5C478NL

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVTFS5C478NLWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage			V_{DSS}	40	V	
Gate-to-Source Voltage			V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3, 4)	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	26	A	
		$T_C = 100^{\circ}\text{C}$		18		
		Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3)	$T_C = 25^{\circ}\text{C}$	P_D	20	W
			$T_C = 100^{\circ}\text{C}$		10	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	10	A	
		$T_A = 100^{\circ}\text{C}$		8.0		
		Power Dissipation $R_{\theta JA}$ (Notes 1, 3)	$T_A = 25^{\circ}\text{C}$	P_D	3.0	W
			$T_A = 100^{\circ}\text{C}$		2.0	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	104	A	
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to +175	$^{\circ}\text{C}$	
Source Current (Body Diode)			I_S	15	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 1.4\text{ A}$)			E_{AS}	43	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 3)	$R_{\theta JC}$	8.2	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	51	

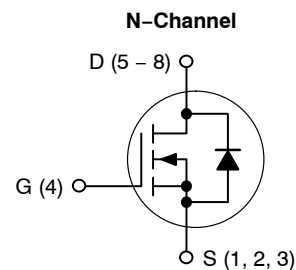
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



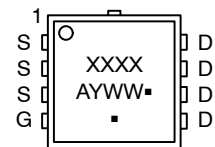
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	14 mΩ @ 10 V	26 A
	25 mΩ @ 4.5 V	



MARKING DIAGRAM



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVTFS5C478NL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25°C		10	μA
			T _J = 125°C		250	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 20 μA	1.2		2.2	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A		11.5	14	mΩ
		V _{GS} = 4.5 V, I _D = 5 A		20	25	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 15 A		25		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		400		pF
Output Capacitance	C _{oss}			170		
Reverse Transfer Capacitance	C _{rss}			8.0		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 32 V, I _D = 15 A		3.8		nC
Threshold Gate Charge	Q _{G(TH)}			1.0		
Gate-to-Source Charge	Q _{GS}			1.9		
Gate-to-Drain Charge	Q _{GD}			1.2		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 15 A		8.0		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DS} = 32 V, I _D = 15 A, R _G = 2.5 Ω		7.0		ns
Rise Time	t _r			39		
Turn-Off Delay Time	t _{d(off)}			14		
Fall Time	t _f			5.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.85	1.2	V
			T _J = 125°C		0.70		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 15 A		15		ns	
Charge Time	t _a			7.0			
Discharge Time	t _b			8.0			
Reverse Recovery Charge	Q _{RR}			5.0			nC

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

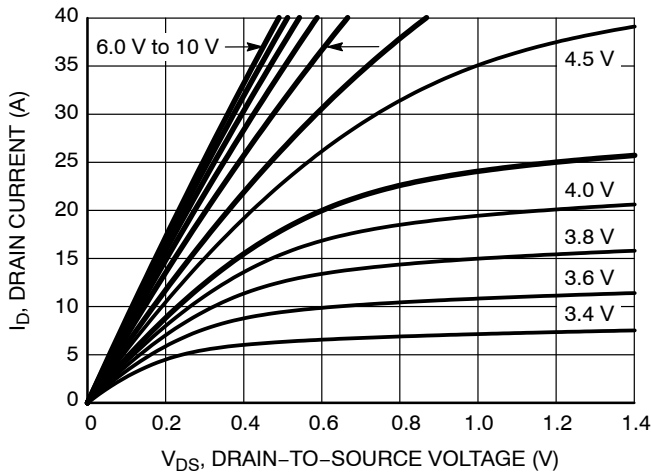


Figure 1. On-Region Characteristics

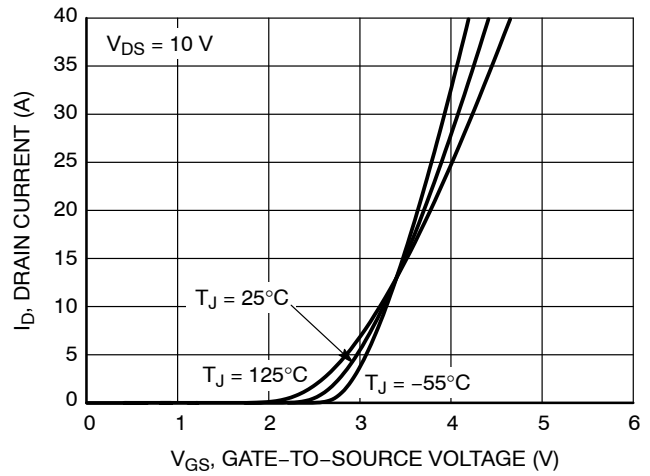


Figure 2. Transfer Characteristics

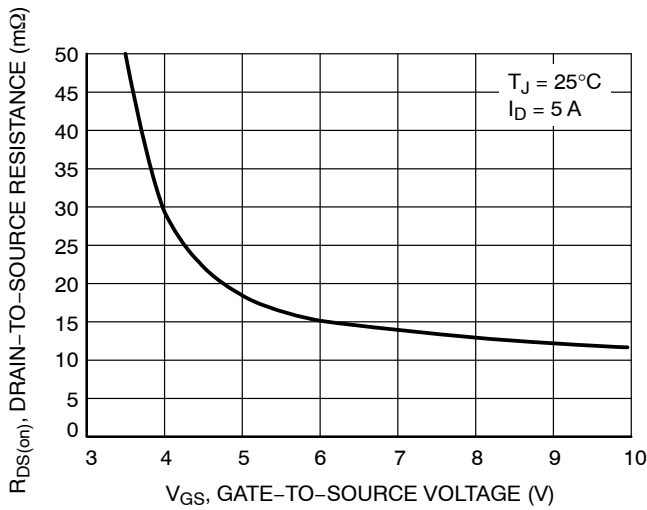


Figure 3. On-Resistance vs. Gate-to-Source Voltage

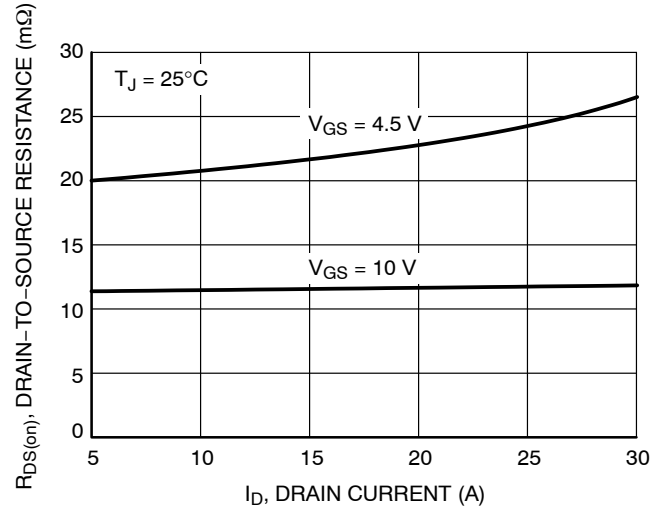


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

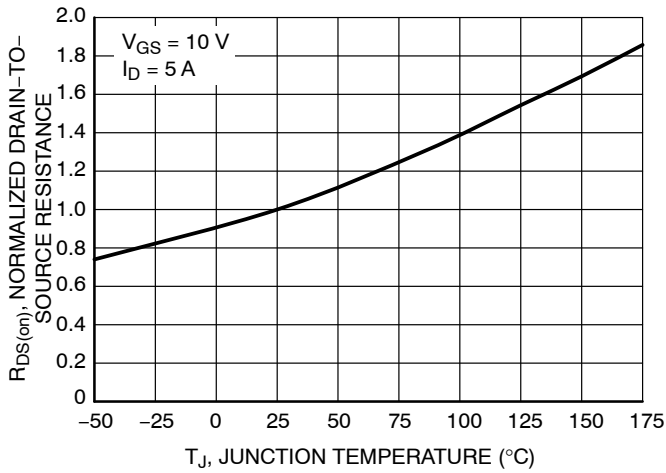


Figure 5. On-Resistance Variation with Temperature

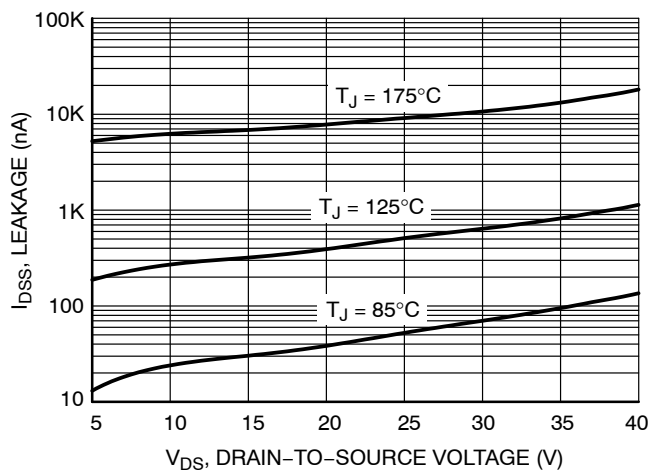


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

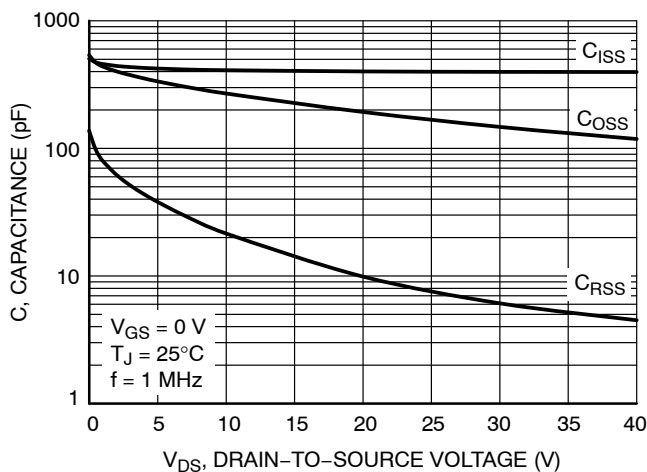


Figure 7. Capacitance Variation

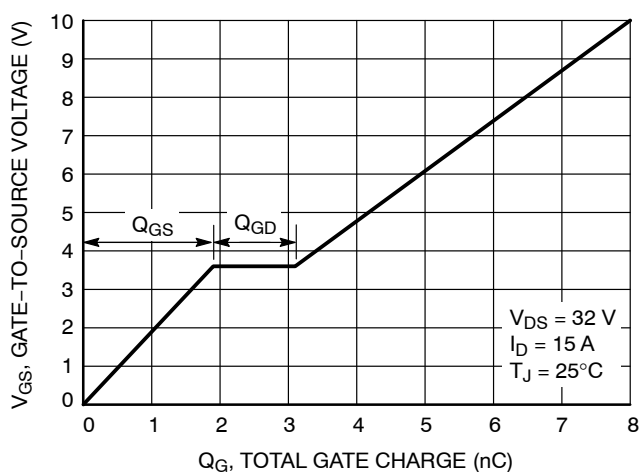


Figure 8. Gate-to-Source Voltage vs. Total Charge

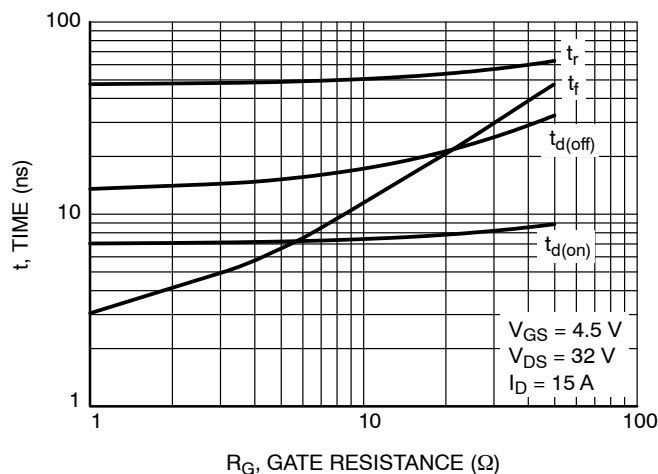


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

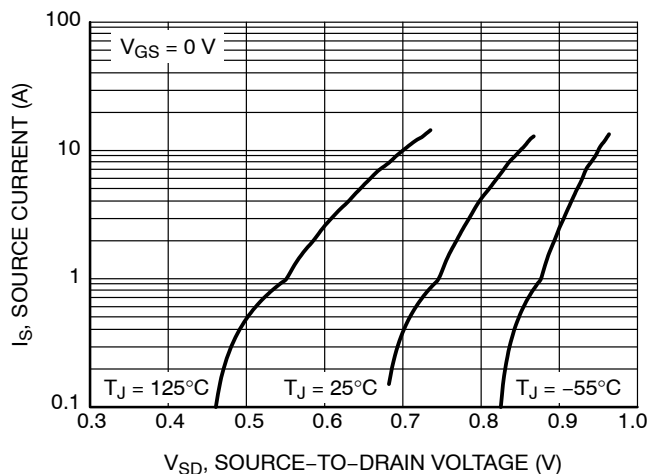


Figure 10. Diode Forward Voltage vs. Current

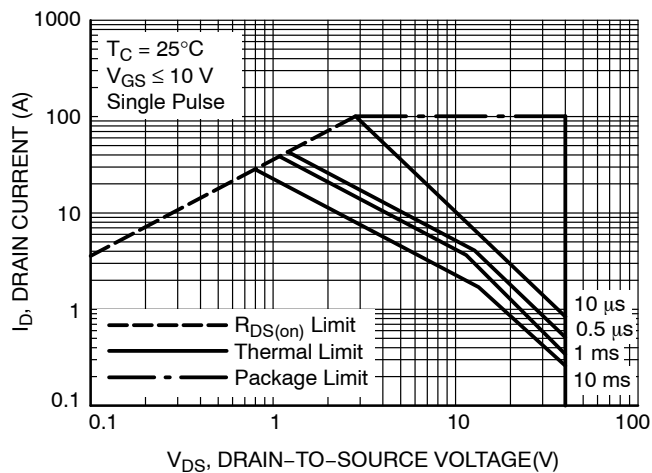


Figure 11. Maximum Rated Forward Biased Safe Operating Area

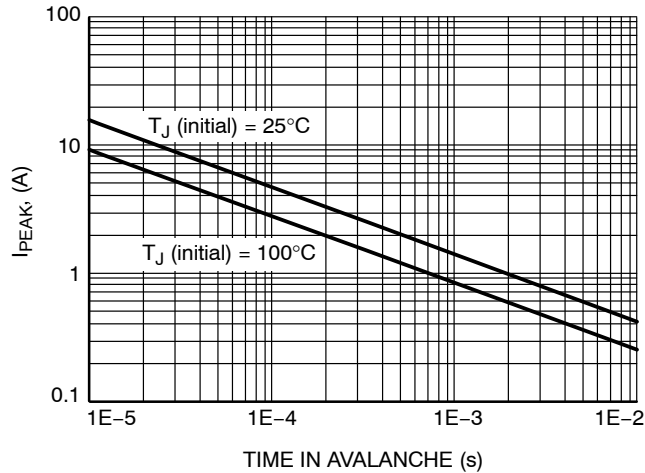


Figure 12. I_{PEAK} vs. Time in Avalanche

NVTFS5C478NL

TYPICAL CHARACTERISTICS

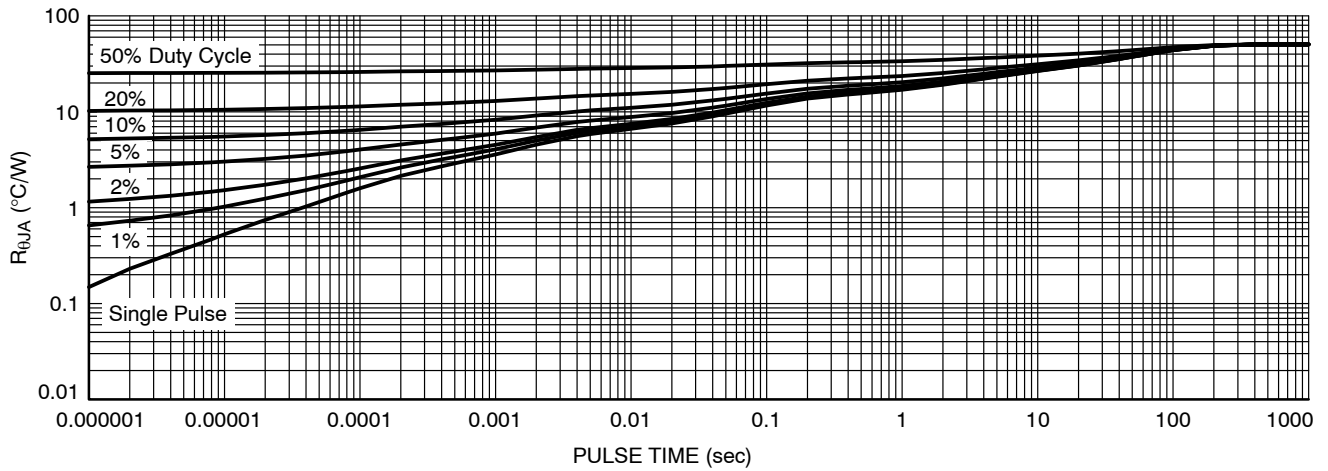


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVTFS5C478NLTAG	478L	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS5C478NLWFTAG	78LW	WDFN8 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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